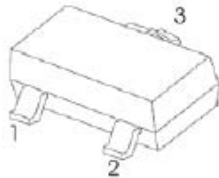


FEATURE

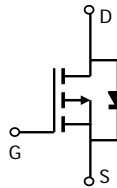
- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

SOT-23



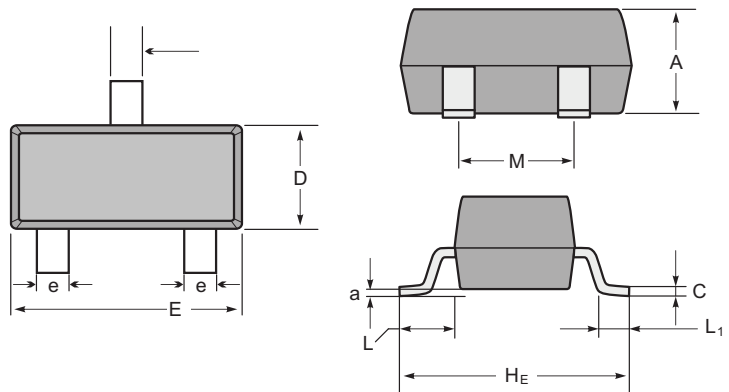
1. GATE
2. SOURCE
3. DRAIN

Equivalent Circuit



Marking

Type number	Marking code
AO3401A	A19T



SOT-23 mechanical data

UNIT		A	C	D	E	H _E	e	M	L	L ₁	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-4.2	A
Power Dissipation	P_D	1.2	W
Thermal Resistance from Junction to Ambient (t<5s)	$R_{\theta JA}$	313	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$

AO3401A

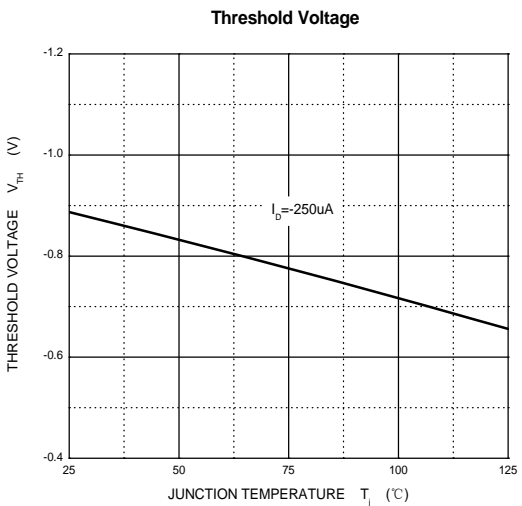
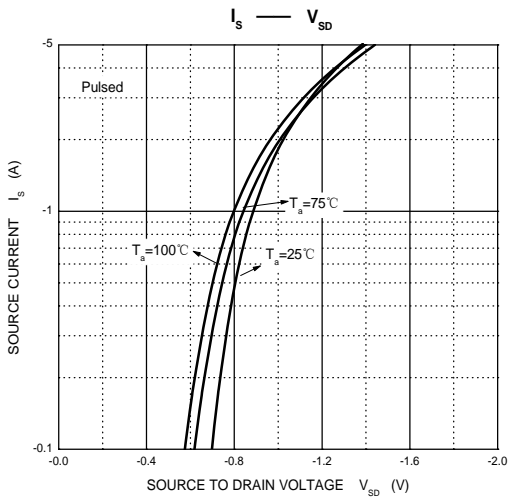
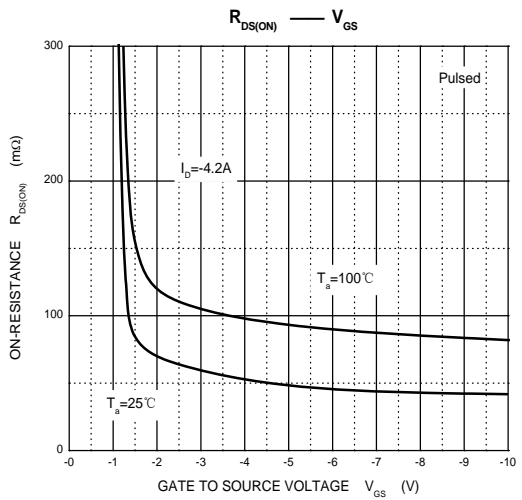
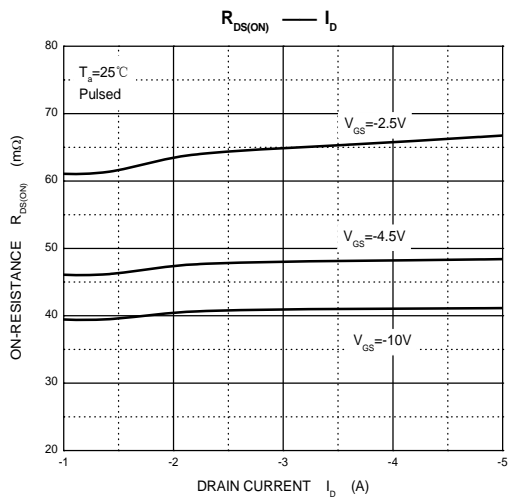
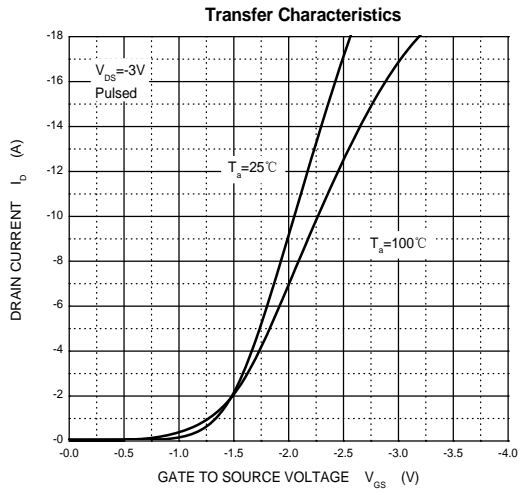
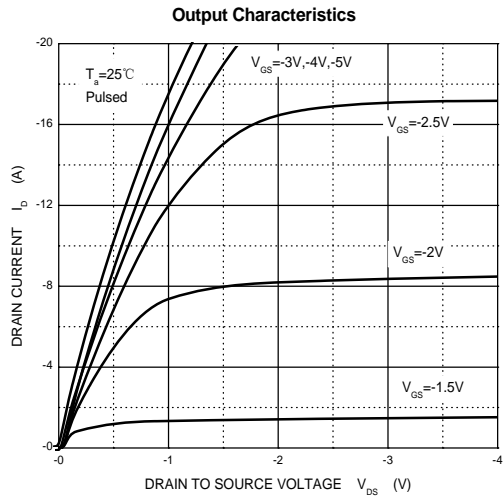
$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$			-1	μA
Gate-source leakage current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
On characteristics						
Drain-source on-resistance (note 1)	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -4.2A$		41	60	m Ω
		$V_{GS} = -4.5V, I_D = -4A$		47	70	m Ω
		$V_{GS} = -2.5V, I_D = -1A$		61	85	m Ω
Forward tranconductance (note 1)	g_{FS}	$V_{DS} = -5V, I_D = -5A$	7			S
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.7		-1.3	V
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		1050		pF
Output capacitance	C_{oss}			127		pF
Reverse transfer capacitance	C_{rss}			85		pF
Switching characteristics (note 2)						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = -10V, V_{DS} = -15V,$ $R_L = 3.6\Omega, R_{GEN} = 6\Omega$			6.5	ns
Turn-on rise time	t_r				3.5	ns
Turn-off delay time	$t_{d(off)}$				40	ns
Turn-off fall Time	t_f				13	ns
Drain-source diode characteristics and maximum ratings						
Diode forward voltage (note 1)	V_{SD}	$I_S = -1A, V_{GS} = 0V$			-1	V

Note :

1. Pulse Test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
2. These parameters have no way to verify.

RATING AND CHARACTERISTIC CURVES (AO3401A)



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